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(71) Applicant (for all designated States except US): **ADAPTIVE PLASMA TECHNOLOGY CORPORATION**
[KR/KR]; 1 Yeongtong-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do 443-808 (KR).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **KIM, Nam-hun**
[KR/KR]; 804-302 Byeokjeokgol Dusan Apt., 973-3 Yeongtong-dong, Paldal-gu, Suwon-si, Gyeonggi-do 442-470 (KR).

(74) Agent: **AJU INTERNATIONAL LAW & PATENT GROUP**; 12th Floor, Poonglim Building, 823-1 Yeoksam-dong, Kangnam-gu, Seoul 135-784 (KR).

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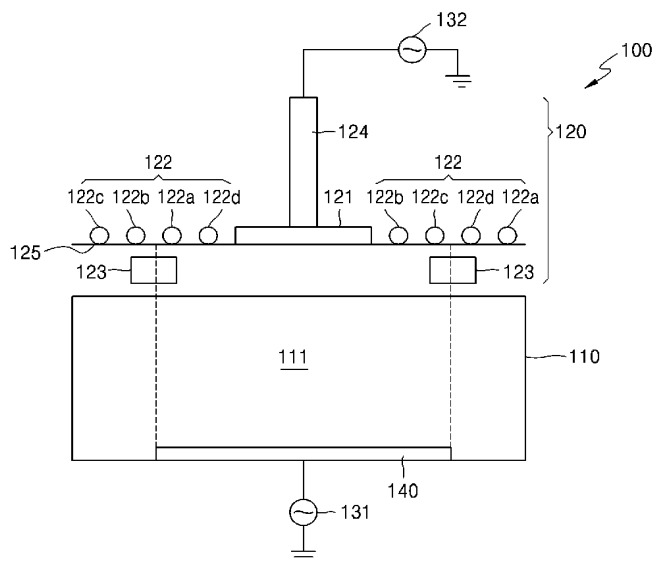
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(54) Title: PLASMA CHAMBER HAVING PLASMA SOURCE COIL AND METHOD FOR ETCHING THE WAFER USING THE SAME



(57) Abstract: A plasma chamber having a plasma source coil includes a chamber body, a plasma source coil, and an edge bushing. The chamber body includes a reaction space, which is limited by a sidewall, a lower exterior wall, and an upper dome, and forms plasma. The plasma source coil arranged on the dome includes M unit coils corresponding to an integer greater than "2". The M unit coils having a predetermined turning number "n" indicative of a positive integer are extended from a center bushing having a predetermined radius at a center part, and are spirally arranged along a circumference of the center bushing, such that the plasma is formed in the reaction space. The edge bushing arranged between the dome of the chamber body and the plasma source coil, and is configured in the form of a cylindrical shape to overlap with an edge of the wafer arranged in the reaction space.

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